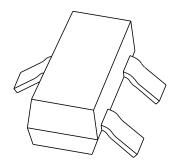
#### DISCRETE SEMICONDUCTORS

# DATA SHEET



## PMBD7000 High-speed double diode

Product specification Supersedes data of November 1993 File under Discrete Semiconductors, SC01 1996 Apr 19





## **High-speed double diode**

#### **PMBD7000**

#### **FEATURES**

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA
- Forward voltage: max. 1 V.

#### **APPLICATIONS**

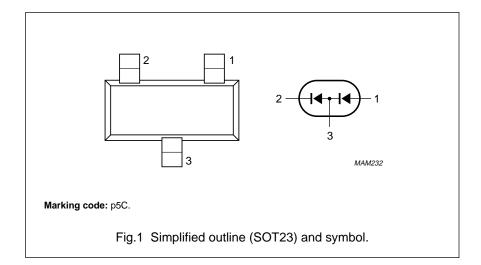
• High-speed switching in e.g. surface mounted circuits.

#### **DESCRIPTION**

The PMBD7000 consists of two high-speed switching diodes connected in series, fabricated in planar technology, and encapsulated in the small plastic SMD SOT23 package.

#### **PINNING**

PIN	DESCRIPTION	
1	anode	
2	cathode	
3	common connection	



#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		_	100	V
V <sub>R</sub>	continuous reverse voltage		_	100	V
I <sub>F</sub>	continuous forward current	single diode loaded; see Fig.2; note 1	_	215	mA
		double diode loaded; see Fig.2; note 1	_	125	mA
I <sub>FRM</sub>	repetitive peak forward current		_	450	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature			150	°C

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#### Note

1. Device mounted on an FR4 printed-circuit board.

## High-speed double diode

PMBD7000

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 1 mA	550	700	mV
		I <sub>F</sub> = 10 mA	670	820	mV
		I <sub>F</sub> = 50 mA	_	1.0	V
		I <sub>F</sub> = 100 mA	0.75	1.10	V
		I <sub>F</sub> = 150 mA	_	1.25	mV
I <sub>R</sub>	reverse current	see Fig.5			
		V <sub>R</sub> = 50 V	_	300	nA
		V <sub>R</sub> = 100 V	_	500	nA
		V <sub>R</sub> = 50 V; T <sub>j</sub> = 150 °C	_	100	μΑ
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.6	_	1.5	pF
t <sub>rr</sub>	reverse recovery time	when switched from I <sub>F</sub> = 10 mA to	_	4	ns
		$I_R$ = 10 mA; $R_L$ = 100 Ω; measured at $I_R$ = 1 mA; see Fig.7			
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	_	1.75	V

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Device mounted on an FR4 printed-circuit board.

## High-speed double diode

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#### **GRAPHICAL DATA**

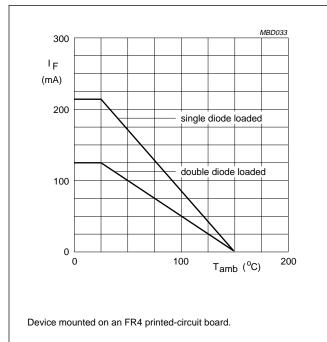
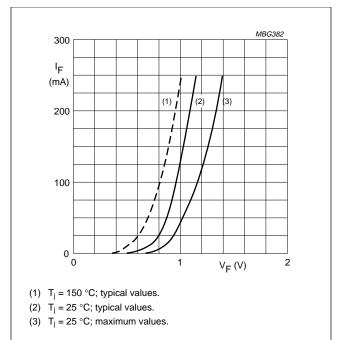
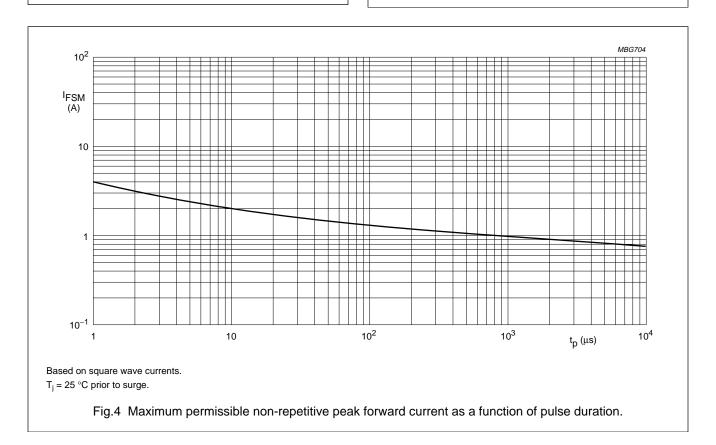


Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



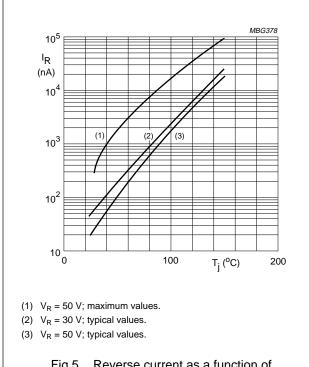
Forward current as a function of

forward voltage.



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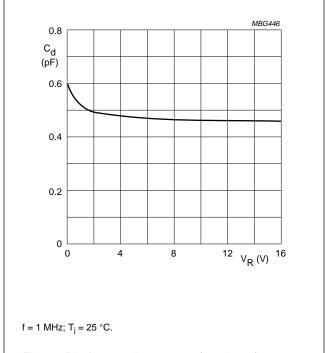
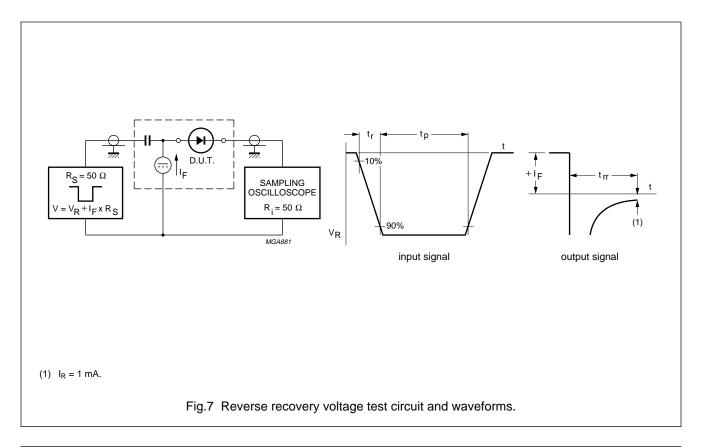


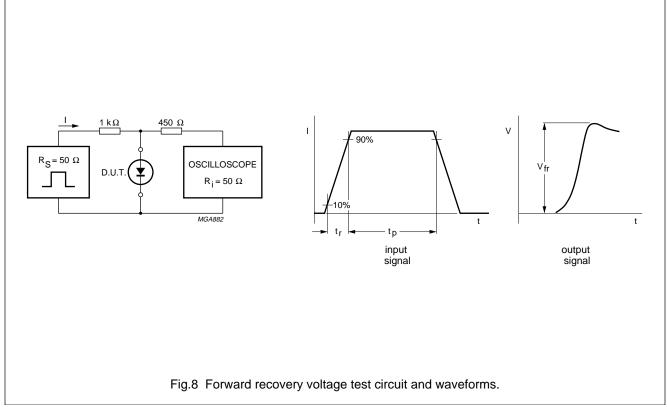
Fig.5 Reverse current as a function of junction temperature.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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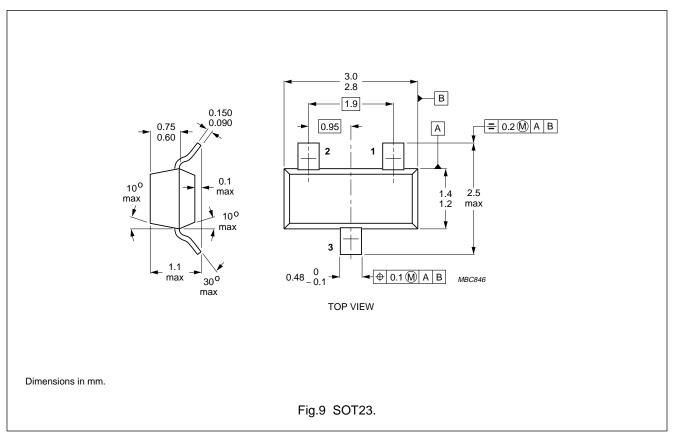




### High-speed double diode

**PMBD7000** 

#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

Data Sheet Status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation			

more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.